

# Supporting Materials for Enhanced thermoelectric properties of Ga-doped $\text{In}_2\text{O}_3$ ceramics via synergetic band gap engineering and phonon suppression

Yong Liu<sup>a,b,†</sup>, Wei Xu<sup>c</sup>, Da-Bo Liu<sup>a</sup>, Meijuan Yu<sup>c</sup>, Yuan-Hua Lin<sup>b,†</sup>, and Ce-Wen Nan<sup>b</sup>

<sup>a</sup>AVIC Beijing Institute of Aeronautical Materials, Beijing 100095, China.

<sup>b</sup>State Key Laboratory of New Ceramics and Fine Processing, Department of Materials Science and Engineering, Tsinghua University, Beijing, 100084, China.

<sup>c</sup>Beijing Synchrotron Radiation Facility, Institute of High Energy Physics, Chinese Academy of Sciences, 100049, China.

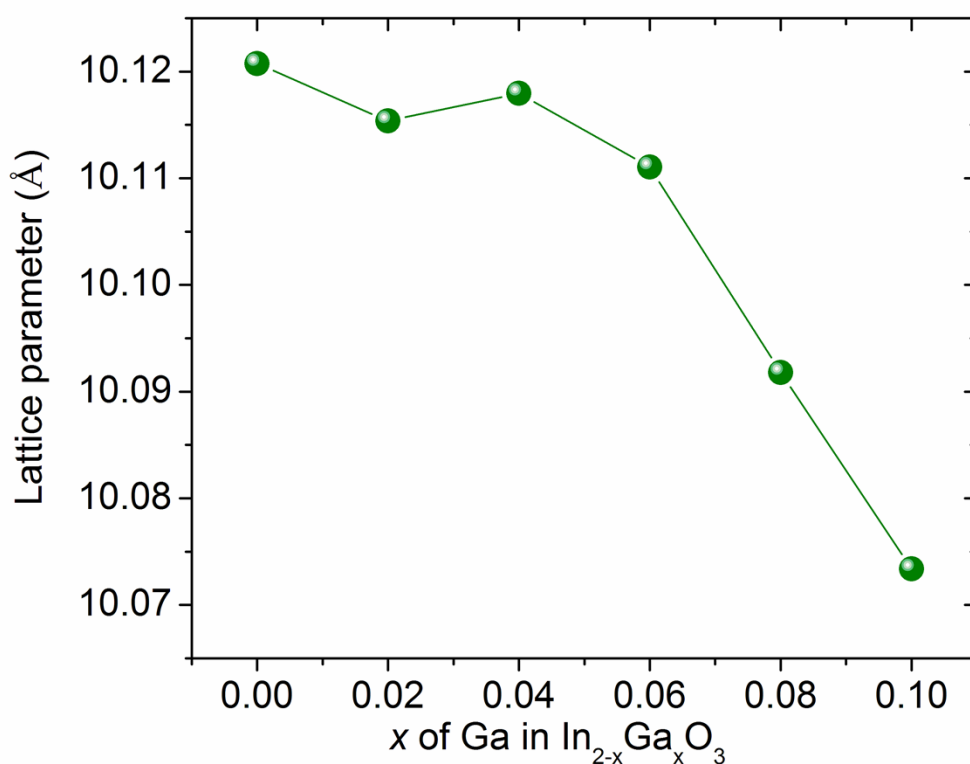


Figure.S1 The refined lattice constant versus the doping concentration in  $\text{In}_{2-x}\text{Ga}_x\text{O}_3$

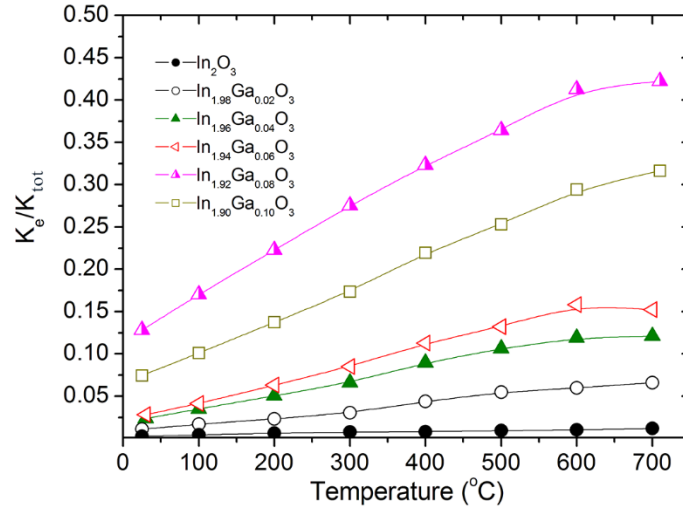


Figure. S2 Comparison of the proportion of  $\kappa_e$  (the electrical contribution of thermal conductivity) in  $\kappa_{tot}$  (the total thermal conductivity) for pure and doped  $In_2O_3$  ceramics.